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Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Details

E·XE

Product Status	Not For New Designs
Core Processor	C166SV2
Core Size	16/32-Bit
Speed	66MHz
Connectivity	CANbus, EBI/EMI, I ² C, LINbus, SPI, UART/USART
Peripherals	I ² S, POR, PWM, WDT
Number of I/O	48
Program Memory Size	166KB (166K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	12K x 8
Voltage - Supply (Vcc/Vdd)	3V ~ 5.5V
Data Converters	A/D 19x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 125°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP Exposed Pad
Supplier Device Package	PG-LQFP-64-22
Purchase URL	https://www.e-xfl.com/product-detail/infineon-technologies/xc2733x20f66Iraakxuma1

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Summary of Features

16/32-Bit Single-Chip Microcontroller with 32-Bit Performance XC2733X (XC2000 Family)

1 Summary of Features

For a quick overview and easy reference, the features of the XC2733X are summarized here.

- High-performance CPU with five-stage pipeline and MPU
 - 12.5 ns instruction cycle @ 80 MHz CPU clock (single-cycle execution)
 - One-cycle 32-bit addition and subtraction with 40-bit result
 - One-cycle multiplication (16 × 16 bit)
 - Background division (32 / 16 bit) in 21 cycles
 - One-cycle multiply-and-accumulate (MAC) instructions
 - Enhanced Boolean bit manipulation facilities
 - Zero-cycle jump execution
 - Additional instructions to support HLL and operating systems
 - Register-based design with multiple variable register banks
 - Fast context switching support with two additional local register banks
 - 16 Mbytes total linear address space for code and data
 - 1,024 Bytes on-chip special function register area (C166 Family compatible)
 - Integrated Memory Protection Unit (MPU)
- Interrupt system with 16 priority levels providing 64 interrupt nodes
 - Selectable external inputs for interrupt generation and wake-up
 - Fastest sample-rate 12.5 ns
- Eight-channel interrupt-driven single-cycle data transfer with Peripheral Event Controller (PEC), 24-bit pointers cover total address space
- Clock generation from internal or external clock sources, using on-chip PLL or prescaler
- Hardware CRC-Checker with Programmable Polynomial to Supervise On-Chip Memory Areas
- On-chip memory modules
 - 2 Kbytes on-chip dual-port RAM (DPRAM)
 - 6 Kbytes on-chip data SRAM (DSRAM)
 - 4 Kbytes on-chip program/data SRAM (PSRAM)
 - Up to 160 Kbytes on-chip program memory (Flash memory)
 - Memory content protection through Error Correction Code (ECC) for Flash memory and through parity for RAMs



Summary of Features

1.2 Special Device Types

Special device types are only available for high-volume applications on request.

Table 2 Synopsis of XC2733X Special Device Types

Derivative ¹⁾	Flash Memory ²⁾	PSRAM DSRAM ³⁾	Capt./Comp. Modules	ADC ⁴⁾ Chan.	Interfaces ⁴⁾
XC2733X-20FxL	160 Kbytes	4 Kbytes 6 Kbytes	CC2 CCU60/3	19	2 CAN Nodes, 4 Serial Chan.

1) x is a placeholder for available speed grade in MHz. Can be 66 or 80.

2) Specific information about the on-chip Flash memory in Table 3.

3) All derivatives additionally provide 2 Kbytes DPRAM.

4) Specific information about the available channels in Table 5.



General Device Information

Table	Table 6 Pin Definitions and Functions (cont'd)					
Pin	Symbol	Ctrl.	Туре	Function		
34	P2.6	O0 / I	St/B	Bit 6 of Port 2, General Purpose Input/Output		
	U0C0_SELO 0	01	St/B	USIC0 Channel 0 Select/Control 0 Output		
	U0C1_SELO 1	O2	St/B	USIC0 Channel 1 Select/Control 1 Output		
	CC2_CC19	O3 / I	St/B	CAPCOM2 CC19IO Capture Inp./ Compare Out.		
	CLKIN1	I	St/B	Clock Signal Input 1		
	U0C0_DX2D	I	St/B	USIC0 Channel 0 Shift Control Input		
	RxDC0D	I	St/B	CAN Node 0 Receive Data Input		
	ESR2_6	I	St/B	ESR2 Trigger Input 6		
35	P2.7	O0 / I	St/B	Bit 7 of Port 2, General Purpose Input/Output		
	U0C1_SELO 0	01	St/B	USIC0 Channel 1 Select/Control 0 Output		
	U0C0_SELO 1	O2	St/B	USIC0 Channel 0 Select/Control 1 Output		
	CC2_CC20	O3 / I	St/B	CAPCOM2 CC20IO Capture Inp./ Compare Out.		
	U0C1_DX2C	I	St/B	USIC0 Channel 1 Shift Control Input		
	ESR2_7	I	St/B	ESR2 Trigger Input 7		
	RxDC1C	I	St/B	CAN Node 1 Receive Data Input		
	U1C0_DX0A	I	St/B	USIC1 Channel 0 Shift Data Input		
36	P2.8	O0 / I	St/B	Bit 8 of Port 2, General Purpose Input/Output		
	U0C1_SCLK OUT	01	St/B	USIC0 Channel 1 Shift Clock Output		
	EXTCLK	O2	St/B	Programmable Clock Signal Output		
	CC2_CC21	O3 / I	St/B	CAPCOM2 CC21IO Capture Inp./ Compare Out.		
	U0C1_DX1D	I	St/B	USIC0 Channel 1 Shift Clock Input		
37	P2.9	O0 / I	St/B	Bit 9 of Port 2, General Purpose Input/Output		
	U0C1_DOUT	01	St/B	USIC0 Channel 1 Shift Data Output		
	TxDC1	O2	St/B	CAN Node 1 Transmit Data Output		
	CC2_CC22	O3 / I	St/B	CAPCOM2 CC22IO Capture Inp./ Compare Out.		
	C1	I	St/B	Configuration Pin 1		
	TCK_A	I	St/B	DAP0/JTAG Clock Input		



3 Functional Description

The architecture of the XC2733X combines advantages of RISC, CISC, and DSP processors with an advanced peripheral subsystem in a well-balanced design. On-chip memory blocks allow the design of compact systems-on-silicon with maximum performance suited for computing, control, and communication.

The on-chip memory blocks (program code memory and SRAM, dual-port RAM, data SRAM) and the generic peripherals are connected to the CPU by separate high-speed buses. Another bus, the LXBus, connects additional on-chip resources and external resources (see **Figure 3**). This bus structure enhances overall system performance by enabling the concurrent operation of several subsystems of the XC2733X.

The block diagram gives an overview of the on-chip components and the advanced internal bus structure of the XC2733X.



Figure 3 Block Diagram



6 Kbytes of on-chip Data SRAM (DSRAM) are used for storage of general user data. The DSRAM is accessed via a separate interface and is optimized for data access.

2 Kbytes of on-chip Dual-Port RAM (DPRAM) provide storage for user-defined variables, for the system stack, and for general purpose register banks. A register bank can consist of up to 16 word-wide (R0 to R15) and/or byte-wide (RL0, RH0, ..., RL7, RH7) General Purpose Registers (GPRs).

The upper 256 bytes of the DPRAM are directly bit addressable. When used by a GPR, any location in the DPRAM is bit addressable.

1024 bytes (2 \times **512 bytes)** of the address space are reserved for the Special Function Register areas (SFR space and ESFR space). SFRs are word-wide registers which are used to control and monitor functions of the different on-chip units. Unused SFR addresses are reserved for future members of the XC2000 Family. In order to ensure upward compatibility they should either not be accessed or written with zeros.

The on-chip Flash memory stores code, constant data, and control data. The 160 Kbytes of on-chip Flash memory consist of 1 module of 32 Kbytes (preferably for data storage) and 1 module of 128 Kbytes. Each module is organized in 4-Kbyte sectors. The uppermost 4-Kbyte sector of segment 0 (located in Flash module 0) is used internally to store operation control parameters and protection information.

Each sector can be separately write protected¹⁾, erased and programmed (in blocks of 128 Bytes). The complete Flash area can be read-protected. A user-defined password sequence temporarily unlocks protected areas. The Flash modules combine 128-bit read access with protected and efficient writing algorithms for programming and erasing. Dynamic error correction provides extremely high read data security for all read access operations. Access to different Flash modules can be executed in parallel. For Flash parameters, please see Section 4.6.

Memory Content Protection

The contents of on-chip memories can be protected against soft errors (induced e.g. by radiation) by activating the parity mechanism or the Error Correction Code (ECC).

The parity mechanism can detect a single-bit error and prevent the software from using incorrect data or executing incorrect instructions.

The ECC mechanism can detect and automatically correct single-bit errors. This supports the stable operation of the system.

It is strongly recommended to activate the ECC mechanism wherever possible because this dramatically increases the robustness of an application against such soft errors.

To save control bits, sectors are clustered for protection purposes, they remain separate for programming/erasing.



3.3 Memory Protection Unit (MPU)

The XC2733X's Memory Protection Unit (MPU) protects user-specified memory areas from unauthorized read, write, or instruction fetch accesses. The MPU can protect the whole address space including the peripheral area. This completes established mechanisms such as the register security mechanism or stack overrun/underrun detection.

Four Protection Levels support flexible system programming where operating system, low level drivers, and applications run on separate levels. Each protection level permits different access restrictions for instructions and/or data.

Every access is checked (if the MPU is enabled) and an access violating the permission rules will be marked as invalid and leads to a protection trap.

A set of protection registers for each protection level specifies the address ranges and the access permissions. Applications requiring more than 4 protection levels can dynamically re-program the protection registers.

3.4 Memory Checker Module (MCHK)

The XC2733X's Memory Checker Module calculates a checksum (fractional polynomial division) on a block of data, often called Cyclic Redundancy Code (CRC). It is based on a 32-bit linear feedback shift register and may, therefore, also be used to generate pseudo-random numbers.

The Memory Checker Module is a 16-bit parallel input signature compression circuitry which enables error detection within a block of data stored in memory, registers, or communicated e.g. via serial communication lines. It reduces the probability of error masking due to repeated error patterns by calculating the signature of blocks of data.

The polynomial used for operation is configurable, so most of the commonly used polynomials may be used. Also, the block size for generating a CRC result is configurable via a local counter. An interrupt may be generated if testing the current data block reveals an error.

An autonomous CRC compare circuitry is included to enable redundant error detection, e.g. to enable higher safety integrity levels.

The Memory Checker Module provides enhanced fault detection (beyond parity or ECC) for data and instructions in volatile and non volatile memories. This is especially important for the safety and reliability of embedded systems.



XC2733X XC2000 Family / Econo Line

Functional Description



Figure 5 CAPCOM Unit Block Diagram



3.8 Capture/Compare Units CCU6x

The XC2733X types feature the CCU60 and CCU63 units.

CCU6 is a high-resolution capture and compare unit with application-specific modes. It provides inputs to start the timers synchronously, an important feature in devices with several CCU6 modules.

The module provides two independent timers (T12, T13), that can be used for PWM generation, especially for AC motor control. Additionally, special control modes for block commutation and multi-phase machines are supported.

Timer 12 Features

- Three capture/compare channels, where each channel can be used either as a capture or as a compare channel.
- Supports generation of a three-phase PWM (six outputs, individual signals for highside and low-side switches)
- 16-bit resolution, maximum count frequency = peripheral clock
- Dead-time control for each channel to avoid short circuits in the power stage
- Concurrent update of the required T12/13 registers
- Center-aligned and edge-aligned PWM can be generated
- Single-shot mode supported
- Many interrupt request sources
- Hysteresis-like control mode
- Automatic start on a HW event (T12HR, for synchronization purposes)

Timer 13 Features

- One independent compare channel with one output
- 16-bit resolution, maximum count frequency = peripheral clock
- Can be synchronized to T12
- Interrupt generation at period match and compare match
- Single-shot mode supported
- Automatic start on a HW event (T13HR, for synchronization purposes)

Additional Features

- Block commutation for brushless DC drives implemented
- Position detection via Hall sensor pattern
- Automatic rotational speed measurement for block commutation
- Integrated error handling
- Fast emergency stop without CPU load via external signal (CTRAP)
- Control modes for multi-channel AC drives
- Output levels can be selected and adapted to the power stage



With its maximum resolution of 2 system clock cycles, the **GPT2 module** provides precise event control and time measurement. It includes two timers (T5, T6) and a capture/reload register (CAPREL). Both timers can be clocked with an input clock which is derived from the CPU clock via a programmable prescaler or with external signals. The counting direction (up/down) for each timer can be programmed by software or altered dynamically with an external signal on a port pin (TxEUD). Concatenation of the timers is supported with the output toggle latch (T6OTL) of timer T6, which changes its state on each timer overflow/underflow.

The state of this latch may be used to clock timer T5, and/or it may be output on pin T6OUT. The overflows/underflows of timer T6 can also be used to clock the CAPCOM2 timers and to initiate a reload from the CAPREL register.

The CAPREL register can capture the contents of timer T5 based on an external signal transition on the corresponding port pin (CAPIN); timer T5 may optionally be cleared after the capture procedure. This allows the XC2733X to measure absolute time differences or to perform pulse multiplication without software overhead.

The capture trigger (timer T5 to CAPREL) can also be generated upon transitions of GPT1 timer T3 inputs T3IN and/or T3EUD. This is especially advantageous when T3 operates in Incremental Interface Mode.



The RTC module can be used for different purposes:

- System clock to determine the current time and date
- Cyclic time-based interrupt, to provide a system time tick independent of CPU frequency and other resources
- 48-bit timer for long-term measurements
- Alarm interrupt at a defined time



Target Protocols

Each USIC channel can receive and transmit data frames with a selectable data word width from 1 to 16 bits in each of the following protocols:

- UART (asynchronous serial channel)
 - module capability: maximum baud rate = f_{SYS} / 4
 - data frame length programmable from 1 to 63 bits
 - MSB or LSB first
- LIN Support (Local Interconnect Network)
 - module capability: maximum baud rate = f_{SYS} / 16
 - checksum generation under software control
 - baud rate detection possible by built-in capture event of baud rate generator
- SSC/SPI (synchronous serial channel with or without data buffer)
 - module capability: maximum baud rate = f_{SYS} / 2, limited by loop delay
 - number of data bits programmable from 1 to 63, more with explicit stop condition
 - MSB or LSB first
 - optional control of slave select signals
- IIC (Inter-IC Bus)
 - supports baud rates of 100 kbit/s and 400 kbit/s
- IIS (Inter-IC Sound Bus)
 - module capability: maximum baud rate = f_{SYS} / 2
- Note: Depending on the selected functions (such as digital filters, input synchronization stages, sample point adjustment, etc.), the maximum achievable baud rate can be limited. Please note that there may be additional delays, such as internal or external propagation delays and driver delays (e.g. for collision detection in UART mode, for IIC, etc.).



3.13 MultiCAN Module

The MultiCAN module contains two independently operating CAN nodes with Full-CAN functionality which are able to exchange Data and Remote Frames using a gateway function. Transmission and reception of CAN frames is handled in accordance with CAN specification V2.0 B (active). Each CAN node can receive and transmit standard frames with 11-bit identifiers as well as extended frames with 29-bit identifiers.

The two CAN nodes share a common set of message objects. Each message object can be individually allocated to either of the CAN nodes. Besides serving as a storage container for incoming and outgoing frames, message objects can be combined to build gateways between the CAN nodes or to set up a FIFO buffer.

The message objects are organized in double-chained linked lists, where each CAN node has its own list of message objects. A CAN node stores frames only into message objects that are allocated to its own message object list and it transmits only messages belonging to this message object list. A powerful, command-driven list controller performs all message object list operations.



Figure 11 Block Diagram of MultiCAN Module



l able 11 lr	istruction Set Summary (cont ^r d)	
Mnemonic	Description	Bytes
ROL/ROR	Rotate left/right direct word GPR	2
ASHR	Arithmetic (sign bit) shift right direct word GPR	2
MOV(B)	Move word (byte) data	2/4
MOVBS/Z	Move byte operand to word op. with sign/zero extension	2/4
JMPA/I/R	Jump absolute/indirect/relative if condition is met	4
JMPS	Jump absolute to a code segment	4
JB(C)	Jump relative if direct bit is set (and clear bit)	4
JNB(S)	Jump relative if direct bit is not set (and set bit)	4
CALLA/I/R	Call absolute/indirect/relative subroutine if condition is met	4
CALLS	Call absolute subroutine in any code segment	4
PCALL	Push direct word register onto system stack and call absolute subroutine	4
TRAP	Call interrupt service routine via immediate trap number	2
PUSH/POP	Push/pop direct word register onto/from system stack	2
SCXT	Push direct word register onto system stack and update register with word operand	4
RET(P)	Return from intra-segment subroutine (and pop direct word register from system stack)	2
RETS	Return from inter-segment subroutine	2
RETI	Return from interrupt service subroutine	2
SBRK	Software Break	2
SRST	Software Reset	4
IDLE	Enter Idle Mode	4
PWRDN	Unused instruction ¹⁾	4
SRVWDT	Service Watchdog Timer	4
DISWDT/ENWE	DT Disable/Enable Watchdog Timer	4
EINIT	End-of-Initialization Register Lock	4
ATOMIC	Begin ATOMIC sequence	2
EXTR	Begin EXTended Register sequence	2
EXTP(R)	Begin EXTended Page (and Register) sequence	2/4
EXTS(R)	Begin EXTended Segment (and Register) sequence	2/4

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Mnemonic	Description	Bytes			
NOP	Null operation	2			
CoMUL/CoMAC	Multiply (and accumulate)	4			
CoADD/CoSUB	Add/Subtract	4			
Co(A)SHR	(Arithmetic) Shift right	4			
CoSHL	Shift left	4			
CoLOAD/STORE	Load accumulator/Store MAC register	4			
CoCMP	Compare	4			
CoMAX/MIN	Maximum/Minimum	4			
CoABS/CoRND	Absolute value/Round accumulator	4			
CoMOV	Data move	4			
CoNEG/NOP	Negate accumulator/Null operation	4			

Table 11 Instruction Set Summary (cont'd)

 The Enter Power Down Mode instruction is not used in the XC2733X, due to the enhanced power control scheme. PWRDN will be correctly decoded, but will trigger no action.



Electrical Parameters

4.1.1 Operating Conditions

The following operating conditions must not be exceeded to ensure correct operation of the XC2733X. All parameters specified in the following sections refer to these operating conditions, unless otherwise noticed.

Note: Typical parameter values refer to room temperature and nominal supply voltage, minimum/maximum parameter values also include conditions of minimum/maximum temperature and minimum/maximum supply voltage. Additional details are described where applicable.

Parameter	Symbol		Values		Unit	Note / Test Condition
		Min.	Тур.	Max.		
Voltage Regulator Buffer Capacitance for DMP_M	$C_{\rm EVRM}$ SR	1.0	-	4.7	μF	1)2)
External Load Capacitance	$C_{L} \operatorname{SR}$	-	20 ³⁾	-	pF	pin out driver= default 4)
System frequency	$f_{\rm SYS}{ m SR}$	-	-	80	MHz	5)
Overload current for analog inputs ⁶⁾	$I_{\rm OVA}{ m SR}$	-2	-	5	mA	not subject to production test
Overload current for digital inputs ⁶⁾	$I_{\rm OVD}{\rm SR}$	-5	-	5	mA	not subject to production test
Overload current coupling factor for analog inputs ⁷)	K _{OVA} CC	-	2.5 x 10 ⁻⁴	1.5 x 10 ⁻³	-	<i>I</i> _{OV} < 0 mA; not subject to production test
		_	1.0 x 10 ⁻⁶	1.0 x 10 ⁻⁴	-	<i>I</i> _{OV} > 0 mA; not subject to production test

Table 13 Operating Conditions



Electrical Parameters

4.3.2 DC Parameters for Lower Voltage Area

Keeping signal levels within the limits specified in this table ensures operation without overload conditions. For signal levels outside these specifications, also refer to the specification of the overload current I_{OV} .

Note: Operating Conditions apply.

Table 17 is valid under the following conditions: $V_{\rm DDP} \ge 3.0$ V; $V_{\rm DDP}$ typ. 3.3 V; $V_{\rm DDP} \le 4.5$ V

Parameter	Symbol		Values		Unit	Note /
		Min.	Тур.	Max.		Test Condition
Pin capacitance (digital inputs/outputs).	$C_{\rm IO}$ CC	-	-	10	pF	not subject to production test
Input Hysteresis ¹⁾	HYS CC	0.07 x V_{DDP}	_	_	V	R _S = 0 Ohm
Absolute input leakage current on pins of analog ports ²⁾	I _{OZ1} CC	_	10	200	nA	$V_{\rm IN}$ > $V_{\rm SS}$; $V_{\rm IN}$ < $V_{\rm DDP}$
Absolute input leakage current for all other pins. 2)3)	I _{OZ2} CC	-	0.2	2	μA	$T_{ m J} \leq$ 110 °C; $V_{ m IN} > V_{ m SS}$; $V_{ m IN} < V_{ m DDP}$
		_	0.2	6	μΑ	$T_{ m J} \leq$ 150 °C; $V_{ m IN} > V_{ m SS}$; $V_{ m IN} < V_{ m DDP}$
Pull Level Force Current ⁴⁾	I _{PLF} SR	150	-	_	μΑ	$ \begin{array}{l} V_{\text{IN}} \geq V_{\text{IHmin}} \\ (pulldown_ena \\ bled); \\ V_{\text{IN}} \leq V_{\text{ILmax}} \\ (pullup_enable \\ d); \end{array} $
Pull Level Keep Current ⁵⁾	I _{PLK} SR	_	-	10	μΑ	$V_{\text{IN}} \ge V_{\text{IHmin}}$ (pullup_enable d); $V_{\text{IN}} \le V_{\text{ILmax}}$ (pulldown_ena bled)

Table 17 DC Characteristics for Lower Voltage Range



XC2733X XC2000 Family / Econo Line

Electrical Parameters





Note: Operating Conditions apply.

Table 19	Leakage Power Consumption
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Parameter	Symbol	Values			Unit	Note /
		Min.	Тур.	Max.		Test Condition
Leakage supply current ¹⁾²⁾	I _{LK1} CC	-	0.03	0.04	mA	<i>T</i> _J = 25 °C
		-	0.4	1.1	mA	<i>T</i> _J = 85 °C
		-	1.7	4.9	mA	<i>T</i> _J = 125 °C
		-	3.5	10.7	mA	<i>T</i> _J = 150 °C

1) The supply current caused by leakage depends mainly on the junction temperature and the supply voltage. The temperature difference between the junction temperature T_J and the ambient temperature T_A must be taken into account. As this fraction of the supply current does not depend on device activity, it must be added to other power consumption values.

2) All inputs (including pins configured as inputs) are set at 0 V to 0.1 V or at V_{DDP} - 0.1 V to V_{DDP} and all outputs (including pins configured as outputs) are disconnected.



Electrical Parameters

4.5 System Parameters

The following parameters specify several aspects which are important when integrating the XC2733X into an application system.

Note: These parameters are not subject to production test but verified by design and/or characterization.

Note: Operating Conditions apply.

Parameter	Symbol		Values		Unit	Note /
		Min.	Тур.	Max.		Test Condition
Short-term deviation of internal clock source frequency ¹⁾	∆f _{INT} CC	-1	-	1	%	$\Delta T_{J} = \le 10^{\circ} C$
Internal clock source frequency	$f_{\rm INT}{\rm CC}$	4.8	5.0	5.2	MHz	
Wakeup clock source	$f_{\rm WU}{ m CC}$	400	-	700	kHz	FREQSEL= 00
frequency ²⁾		210	-	390	kHz	FREQSEL= 01
		140	—	260	kHz	FREQSEL= 10
		110	—	200	kHz	FREQSEL= 11
Startup time from power- on with code execution from Flash	t _{SPO} CC	1.4	1.9	2.4	ms	$f_{\rm WU}$ = 500 kHz
Startup time from stopover mode with code execution from PSRAM	t _{SSO} CC	11 / f _{WU} ³⁾	-	12 / f _{WU} ³⁾	μS	
Core voltage (PVC) supervision level	$V_{\rm PVC}{ m CC}$	V _{LV} - 0.03	$V_{\rm LV}$	V _{LV} + 0.07 ⁴⁾	V	5)
Supply watchdog (SWD) supervision level	V _{SWD} CC	V _{LV} - 0.10 ⁶⁾	$V_{\rm LV}$	V _{LV} + 0.15	V	voltage_range= lower ⁵⁾
		V _{LV} - 0.15	$V_{\rm LV}$	V _{LV} + 0.15	V	voltage_range= upper ⁵⁾

Table 24Various System Parameters

 The short-term frequency deviation refers to a timeframe of a few hours and is measured relative to the current frequency at the beginning of the respective timeframe. This parameter is useful to determine a time span for re-triggering a LIN synchronization.

 This parameter is tested for the fastest and the slowest selection. The medium selections are not subject to production test - verified by design/characterization.

3) f_{WU} in MHz.



Electrical Parameters

4.6 Flash Memory Parameters

The XC2733X is delivered with all Flash sectors erased and with no protection installed. The data retention time of the XC2733X's Flash memory (i.e. the time after which stored data can still be retrieved) depends on the number of times the Flash memory has been erased and programmed.

Note: These parameters are not subject to production test but verified by design and/or characterization.

Note: Operating Conditions apply.

Parameter	Symbol		Values	S	Unit	Note /
		Min.	Тур.	Max.		Test Condition
Parallel Flash module	$N_{\rm PP}{\rm SR}$	-	-	2 ¹⁾		$N_{\rm FL_RD} \leq 1$
program/erase limit depending on Flash read activity		-	-	1 ²⁾		N _{FL_RD} > 1
Flash erase endurance for security pages	$N_{\rm SEC}{ m SR}$	10	-	-	cycle s	$t_{\rm RET} \ge 20$ years
Flash wait states ³⁾	N _{WSFLASH} SR	1	-	-		$f_{SYS} \le 8 \text{ MHz}$
		2	-	-		$f_{SYS} \le 13 \text{ MHz}$
		3	-	-		$f_{\rm SYS}$ \leq 17 MHz
		4	-	-		$f_{\rm SYS}$ > 17 MHz
Erase time per sector/page	t _{ER} CC	-	7 ⁴⁾	8.0	ms	
Programming time per page	t _{PR} CC	-	34)	3.5	ms	
Data retention time	t _{RET} CC	20	-	-	year s	$N_{\rm ER} \le$ 1,000 cycl es
Drain disturb limit	$N_{\rm DD}{ m SR}$	32	-	-	cycle s	

Table 27 Flash Parameters



Package and Reliability

5.3 Quality Declarations

The operation lifetime of the XC2733X depends on the applied temperature profile in application. For a typical example, please refer to **Table 42**; for other profiles, please contact your Infineon counterpart to calculate the specific lifetime within your application.

Table 41Quality Parameters

Parameter	Symbol		Values		Unit	Note /
		Min.	Тур.	Max.		Test Condition
Operation lifetime	t _{OP} CC	-	-	20	а	See Table 42 and Table 43
ESD susceptibility according to Human Body Model (HBM)	$V_{\rm HBM}$ SR	-	-	2000	V	EIA/JESD22- A114-B
Moisture sensitivity level	MSL CC	-	-	3	-	JEDEC J-STD-020C

Table 42 Typical Usage Temperature Profile

Operating Time (Sum = 20 years)	Operating Temperature	Notes
1200 h	$T_{\rm J}$ = 150°C	Normal operation
3600 h	$T_{\rm J} = 125^{\circ}{\rm C}$	Normal operation
7200 h	$T_{\rm J} = 110^{\circ}{\rm C}$	Normal operation
12000 h	$T_{\rm J} = 100^{\circ}{\rm C}$	Normal operation
7 × 21600 h	<i>T</i> _J = 010°C,, 6070°C	Power reduction

Table 43	Long Time Maximum	Storage T	emperature	Profile
	Long Thile maximum	otorago i	omporataro	

Operating Time (Sum = 20 years)	Operating Temperature	Notes
2000 h	$T_{\rm J}$ = 150°C	Normal operation
16000 h	$T_{\rm J} = 125^{\circ}{\rm C}$	Normal operation
6000 h	$T_{\rm J} = 110^{\circ}{\rm C}$	Normal operation
151200 h	$T_{\rm J} \le 150^{\circ}{ m C}$	No operation